

ABSTRACT OF THE DISCLOSURE

A semiconductor light emitting device of the present invention comprises a n-type InP substrate (1), and a stripe structure (10) formed in the stripe shape on the n-type InP substrate (1) and comprised of a n-type InP lower cladding layer (3), an active layer (4) having a resonator in a direction parallel to the n-type InP substrate (1), and a p-type InP upper cladding layer (5). The stripe structure (10) has a photonic crystal structure (2) with concave portions 9 arranged in rectangular lattice shape, and the direction in which the concave portions (9) of the photonic crystal structure (2) are arranged corresponds with a resonator direction. A stripe-shaped upper electrode (6) is formed on the stripe structure (10) to extend in the resonator direction. The semiconductor light emitting device of the present invention so structured is configured to radiate light in the direction perpendicular to the n-type InP substrate (1).